Supporting Information

External electric field treatment for improving morphology and electrical performance of P(NDI2OD-T2)

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Figure S1. UV-vis absorption graphs with original light and parallel, perpendicular linepolarized lights according to external electric field (EEF) intensity

External electric field (kV/cm)		0	0.5	0.75	1	1.5
Doolt oroo	Parallel (A//)	12.72	11.63	11.90	13.05	14.52
Реак агеа	Perpendicular (A_{\perp})	1.87	1.29	1.31	1.53	2.21
Calculated order parameter		0.66	0.73	0.73	0.71	0.65

Table S1. Polarized UV-vis absorbance data: peak area values, order parameters extracted by

 the main absorption peak depending on the external electric field (EEF) intensities



Figure S2. (a) AFM phase images, (b) vertical linecuts at 64, 128, 192 pixels in the x-axis



Figure S3. FWHM trend in the x- and y-axis direction of the FFT analysis peak



Figure S4. (a) AFM height images and (b) phase images with EEF treatment at the intensity of 2 kV/cm



Figure S5. AFM height images in $10 \times 10 \ \mu m$ area



Figure S6. Transfer curves of OFETs according to EEF intensity

External electric field	(kV/cm)	0	0.5	0.75	1	1.5
Electron mobility [µe]	Average	1.69	1.68	2.14	1.58	1.20
(cm ² /Vs)	Maximum	2.61	2.63	3.33	2.26	1.94
Threshold voltage (V)	e [V _{Th}]	18.0	21.2	19.0	18.4	22.4
Contact resistance [R _C] at V _{Th} (Ω)		2.77E+07	2.33E+06	9.60E+05	6.67E+06	3.78E+07

Table S2. Electrical performance depending on the EEF intensity extracted by operatingOFETs

Year	Max. electron mobility [µ _{e,max}] (cm ² /Vs)	Threshold voltage [V _{Th}] (V)	I_{on}/I_{off}	Literature
2011	0.3		107	63
2012	0.96	~30	107	65
2014	0.14	15	10^{4}	62
2014	0.23		10 ³	70
2015	1.28	3.95	10^{4}	61
2016	1.22	41.66	10 ⁵	69
2017	0.061	50	10^{6}	64
2018	1.47	5	10 ⁵	66
2019	3.99	15.22	10^{4}	71
2020	2.78	23.16	10^{4}	59
2021	0.069	55	10 ³	60
2021	2.56			68
2023	0.78	25	10^{6}	67
2023	3.33	19	10^{4}	This work

Table S3. Summary of the reported electrical performance of OFETs based on P(NDI2OD-T2) up to the present date



Figure S7. Electron mobility distribution of OFET measured before and after a 2-year period, comparing samples treated with 0 kV/cm and 0.75 kV/cm



Figure S8. Output curve of OFETs according to EEF intensity



Figure S9. (a) Y-function and (b) contact resistance depending on the gate voltages with or without various EEF treatment